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**April 2014** 

# FDMB3800N Dual N-Channel PowerTrench MOSFET 30V, 4.8A, $40m\Omega$

## **Features**

- Max  $r_{DS(on)}$  = 40m $\Omega$  at  $V_{GS}$  = 10V,  $I_D$  = 4.8A
- Max  $r_{DS(on)}$  = 51m $\Omega$  at  $V_{GS}$  = 4.5V,  $I_D$  = 4.3A
- Fast switching speed
- Low gate Charge
- High performance trench technology for extremely low r<sub>DS(on)</sub>
- High power and current handling capability.
- RoHS Compliant



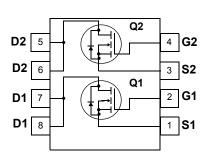
## **General Description**

These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.



MicroFET 3X1.9



## MOSFET Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol		Param		Ratings	Units	
$V_{DS}$	Drain to Source Voltage				30	V
$V_{GS}$	Gate to Source Voltage			±20	V	
	Drain Current	-Continuous	T <sub>A</sub> = 25°C	(Note 1a)	4.8	^
ID	-Pulsed				9	A
Б	Power Dissipation		T <sub>A</sub> = 25°C	Note 1a)	1.6	W
$P_{D}$	Power Dissipation		T <sub>A</sub> = 25°C	(Note 1b)	0.75	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range				-55 to +150	°C

## **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	80	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	165	C/VV

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
3800	FDMB3800N	MicroFET3X1.9	7"	8mm	3000 units

## **Electrical Characteristics** $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions		Тур	Max	Units
Off Chara	octeristics					
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, referenced to 25°C		24		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	Drain Current $V_{DS} = 24V$ , $V_{GS} = 0V$ $T_{J} = 55^{\circ}C$			1 10	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA

## **On Characteristics**

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, referenced to 25°C		-4		mV/°C
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.8A		32	40	
r <sub>DS(on)</sub>	r <sub>DS(on)</sub> Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 4.3A$		41	51	mΩ
	$V_{GS} = 10V, I_D = 4.8A, T_J = 125^{\circ}C$		43	61		
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5V, I_D = 4.8A$		14		S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V -45V V - 0V	350	465	pF
C <sub>oss</sub>	Output Capacitance	─V <sub>DS</sub> =15V, V <sub>GS</sub> = 0V, —f = 1MHz	90	120	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1101112	40	60	pF
$R_g$	Gate Resistance	f = 1MHz	3		Ω

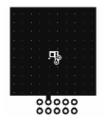
## **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time			8	16	ns
t <sub>r</sub>	Rise Time	$V_{DD}$ = 15V, $I_{D}$ = 1A $V_{GS}$ = 10V, $R_{GEN}$ = 6 $\Omega$		5	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10V, R_{GEN} = 6\Omega$		21	34	ns
t <sub>f</sub>	Fall Time			2	10	ns
$Q_{g(TOT)}$	Total Gate Charge at 5V	V <sub>GS</sub> = 0V to 5V V <sub>DD</sub> = 15V		4	5.6	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	I <sub>D</sub> = 7.5A		1.0		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge			1.5		nC

## **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain - Source Diode Forward Current				1.25	Α
$V_{SD}$	Source to Drain Diode Forward Voltage $V_{GS} = 0V$ , $I_S = 1.25A$ (Note 2)			0.8	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	1 - 4 8 A di/dt - 100 A/v.o		17		ns
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> = 4.8A, di/dt = 100A/μs		7		nC

<sup>1:</sup> R<sub>0JA</sub> is determined with the device mounted on a 1in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0JC</sub> is guaranteed by design while R<sub>0CA</sub> is determined by the user's board design.



a. 80°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 165°C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width <  $300\mu s$ , Duty cycle < 2.0%.

## Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

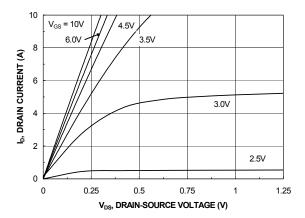


Figure 1. On Region Characteristics

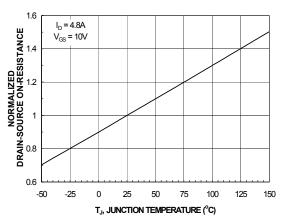


Figure 3. Normalized On - Resistance vs Junction Temperature

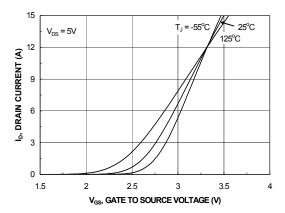


Figure 5. Transfer Characteristics

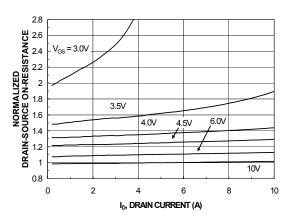


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

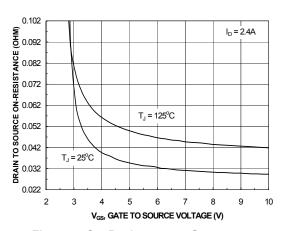


Figure 4. On-Resistance vs Gate to Source Voltage

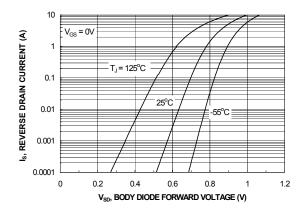


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

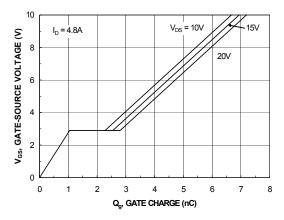


Figure 7. Gate Charge Characteristics

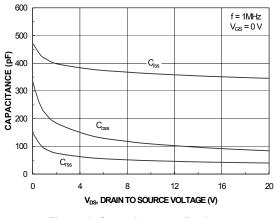


Figure 8. Capacitance vs Drain to Source Voltage

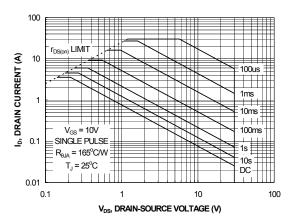


Figure 9. Forward Bias Safe Operating Area

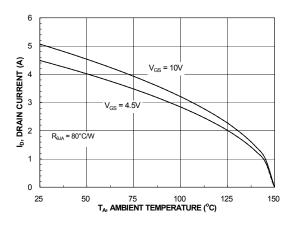


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

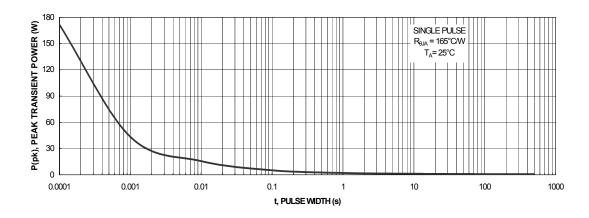


Figure 11. Single Pulse Maximum Power Dissipation

## Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

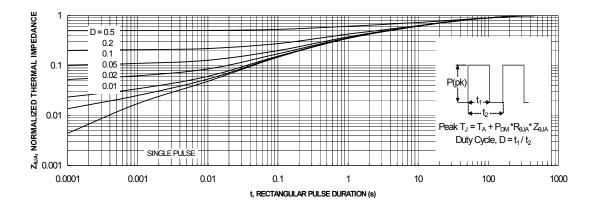
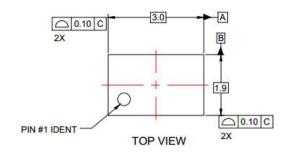
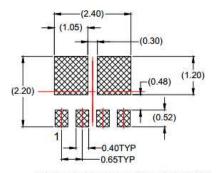


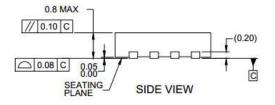
Figure 12. Transient Thermal Response Curve

## **Dimensional Outline and Pad Layout**



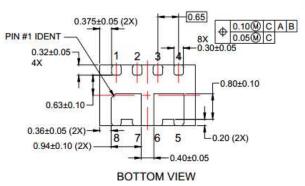


RECOMMENDED LAND PATTERN



### NOTES:

- A DOES NOT FULLY CONFORM TO JEDED REGISTRATION MO-229.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. DRAWING FILENAME: MKT-MKT-MLP08Hrev3.
- E. FAIRCHILD SEMICONDUCTOR.



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